N-Channel Enhancement Mode Field Effect Transistor

Product Summary

ǒ V_{DS} 100V

[illegible]

Electrical Characteristics (T_j=25 unless otherwise noted)

	Symbol					

Typical Performance Characteristics

Figure1. Output Characteristics

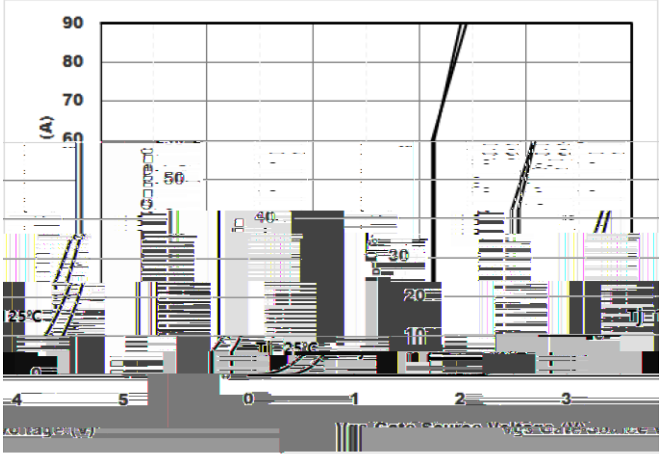

Figure2. Transfer Characteristics

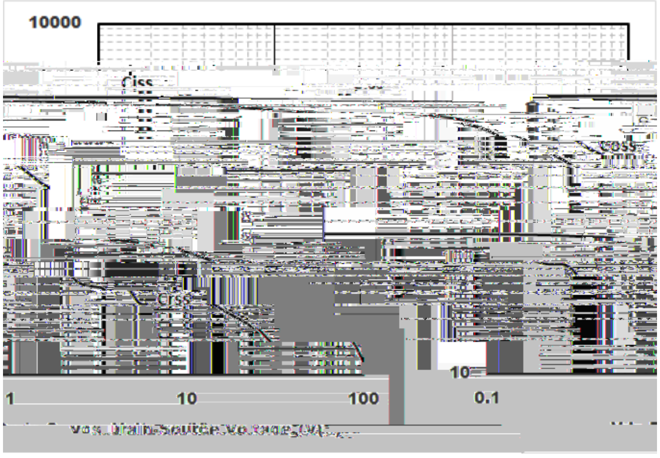

Figure3. Capacitance Characteristics

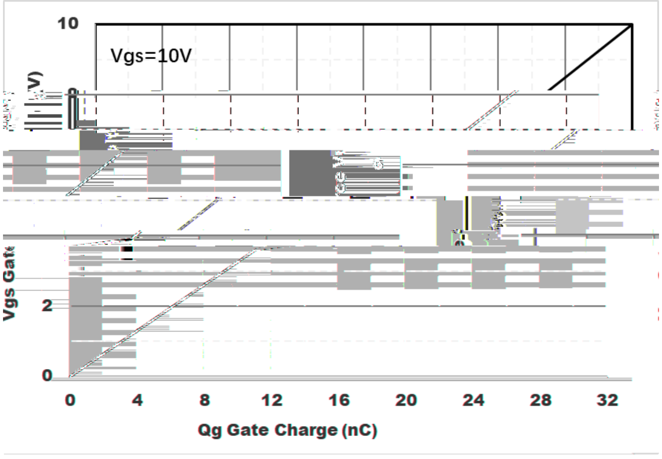

Figure4. Gate Charge

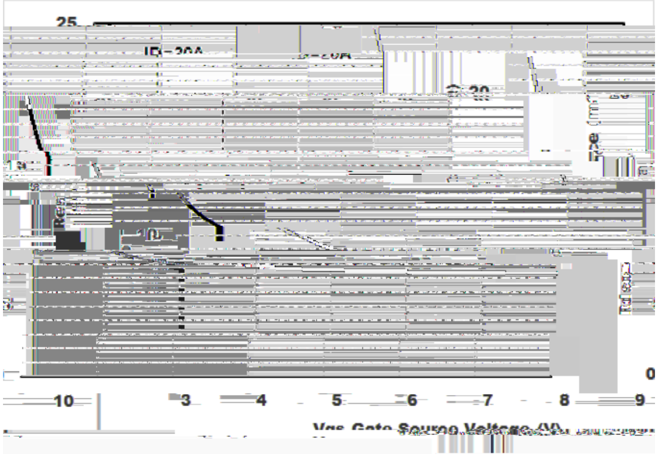

Figure5. On-Resistance vs. Drain Current and Gate Voltage

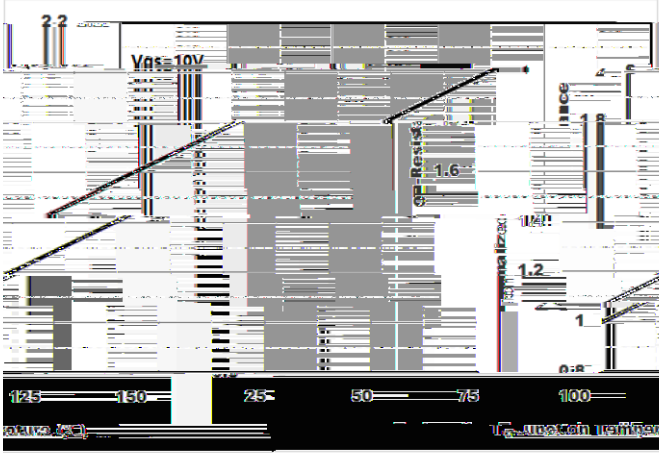

Figure6. Normalized On-Resistance

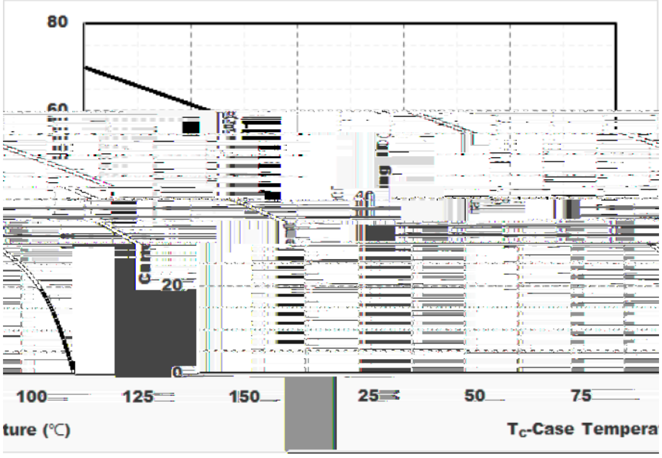

Figure7. Drain current

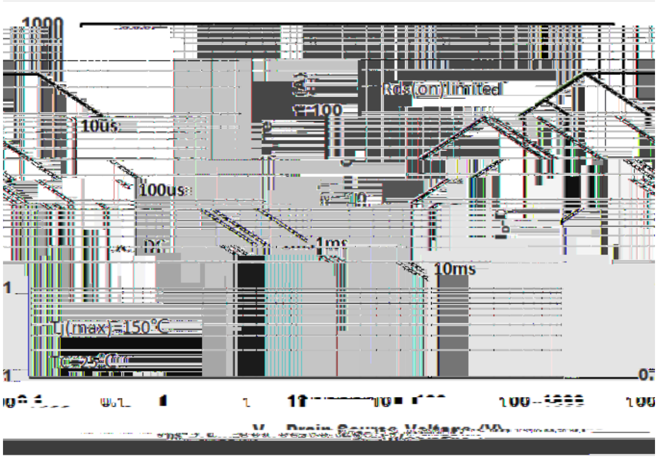

Figure8. Safe Operation Area

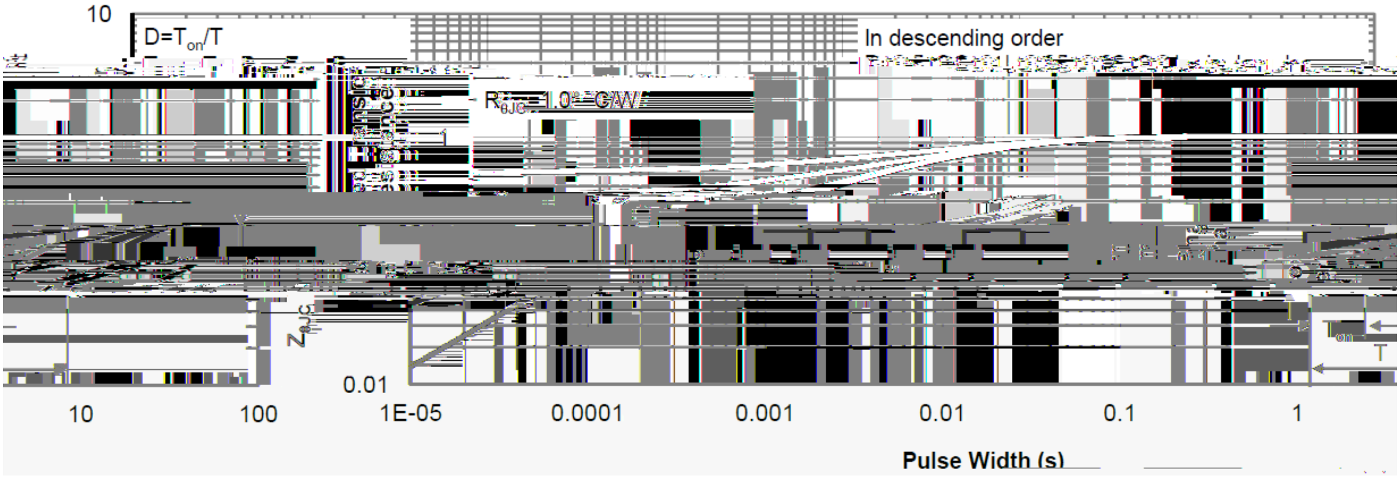

Figure9. Normalized Maximum Transient thermal impedance

√ TO-220AB-C Package information

NOTE:

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